LISTING OF CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

Claims1-18 (Canceled).

Claim 19. (Previously Presented): A method of manufacturing a semiconductor device, comprising the steps of:

creating a separate first opening and a separate third opening completely through an insulating film using a same process;

creating a second opening in said insulating film communicating with said first opening but not said third opening, said second opening being wider than said first opening and having a bottom in said insulating film; and

depositing a first metal film, a dielectric film, and a second metal film, to be stacked in this order above said first opening with only said first metal film being deposited so as to extend into and to fill the first and the third opening so as to form contact plugs to an area exposed by the first and third openings, wherein

said second metal film is operative to serve as an upper electrode, and

at least said first metal film in said second opening is operative to serve as a lower electrode.

20. (New): A method of manufacturing a semiconductor device, comprising the steps of:

creating a separate first opening and a separate third opening completely through an insulating film using a same process;

creating a second opening in said insulating film communicating with said first opening but not said third opening, said second opening being wider than said first opening and having a bottom in said insulating film; and

depositing a first metal film, a dielectric film, and a second metal film, to be stacked in this order above said first opening with said first metal film being deposited so as to extend into the first and the third opening so as to form contact plugs to an area exposed by the first and third openings, wherein

said second metal film is operative to serve as an upper electrode, and

at least said first metal film in said second opening is operative to serve as a lower electrode.